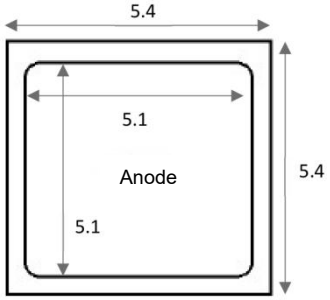


Physical Characteristics

	Die size: 5.4 mm x 5.4 mm (without scribe line) Anode pad open size: 5.1 mm x 5.1 mm Gross die / per 6" wafer = 480 pcs
	Main characteristics: $V_{RRM} = 1200V$ $I_F = 60A$ $Q_C = 300nC$

Mechanical Data

Parameter	Parameter
Nominal Back Metal Composition, Thickness	Ti- Ni - Ag(1.4 μ m)
Nominal Front Metal Composition, Thickness	Al(4.2 μ m)
Wafer Diameter	150mm
Wafer Thickness	175 μ m
Scribe line width	100 μ m
Passivation	Polyimide

Absolute Maximum Ratings($T_C=25^\circ C$, unless otherwise specified)

Parameter	Symbol	Test Condition	Value	Unit
Repetitive Peak Reverse Voltage	V_{RRM}		1200	V
Continuous Forward Current	I_F		60	A
Non-Repetitive Forward Surge Current	I_{FSM}	$t_P = 10ms$	400	A
Repetitive Forward Surge Current	I_{FRM}	$t_P = 10ms$	300	A

Note: These are stress ratings only and functional operation is not implied. Exposure to absolute maximum ratings for prolonged time periods may affect device reliability.

Electrical Specifications($T_C=25^\circ C$, unless otherwise specified)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Reverse Blocking Voltage	V_R	$I_R = 250\mu A$	1200			V
Reverse Current	I_R	$V_R = 1200V, T_J = 25^\circ C$		50	100	μA
		$V_R = 1200V, T_J = 150^\circ C$		160	600	
Forward Voltage	V_F	$I_F = 60A, T_J = 25^\circ C$		1.5	1.7	V
		$I_F = 60A, T_J = 150^\circ C$		2.1	2.5	